



2N6284
2N6287

COMPLEMENTARY SILICON POWER DARLINGTON TRANSISTORS

- STMicroelectronics PREFERRED SALESTYPES
- COMPLEMENTARY PNP - NPN DEVICES
- INTEGRATED ANTIPARALLEL COLLECTOR-EMITTER DIODE

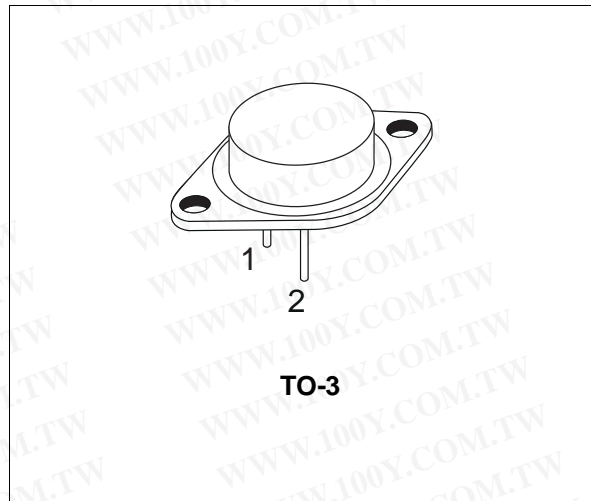
APPLICATIONS

- LINEAR AND SWITCHING INDUSTRIAL EQUIPMENT

DESCRIPTION

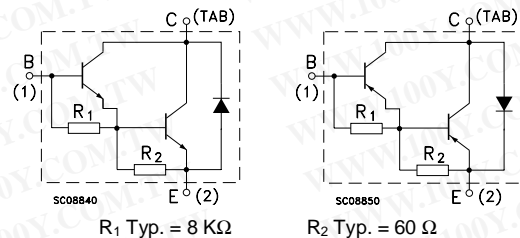
The 2N6284 is a silicon epitaxial-base NPN power transistor in monolithic Darlington configuration mounted in Jedec TO-3 metal case. It is intended for general purpose amplifier and low frequency switching applications.

The complementary PNP types is 2N6287.



勝特力材料 886-3-5753170
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INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		NPN	PNP	
V_{CBO}	Collector-Base Voltage ($I_E = 0$)	2N6284		V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	2N6287		
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	100		V
I_C	Collector Current	5		A
I_{CM}	Collector Peak Current	20		A
I_B	Base Current	40		A
P_{tot}	Total Dissipation at $T_c \leq 25^\circ C$	0.5		W
T_{stg}	Storage Temperature	160		$^\circ C$
T_j	Max. Operating Junction Temperature	-65 to 200		$^\circ C$

For PNP types voltage and current values are negative.

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	1.09	°C/W
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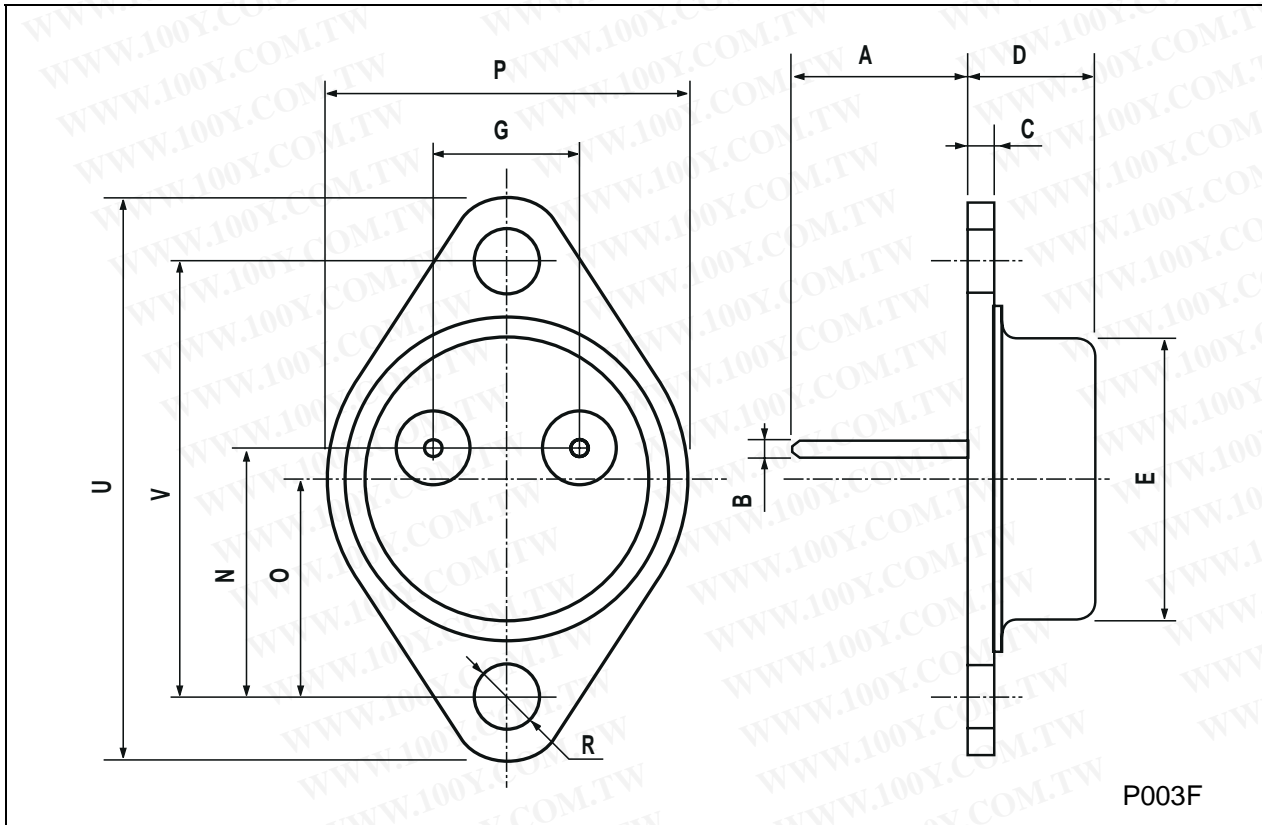
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CEV}	Collector Cut-off Current (V _{BE} = -1.5V)	V _{CE} = rated V _{CEO} V _{CE} = rated V _{CEO} T _c = 150 °C			0.5 5	mA mA
I _{CEO}	Collector Cut-off Current (I _B = 0)	V _{CE} = 50 V			1	mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			2	mA
V _{CEO(sus)*}	Collector-Emitter Sustaining Voltage	I _C = 100 mA	100			V
V _{CE(sat)*}	Collector-Emitter Saturation Voltage	I _C = 10 A I _B = 40 mA I _C = 20 A I _B = 200 mA			2 3	V V
V _{BE(sat)*}	Base-Emitter Saturation Voltage	I _C = 20 A I _B = 200 mA			4	V
V _{BE*}	Base-Emitter Voltage	I _C = 10 A V _{CE} = 3 V			2.8	V
h _{FE*}	DC Current Gain	I _C = 10 A V _{CE} = 3 V I _C = 20 A V _{CE} = 3 V	750 100		18000	
h _{fe}	Small Signal Current Gain	I _C = 3 A V _{CE} = 10 V f = 1KHz	300			
C _{CB0}	Collector Base Capacitance	I _E = 0 V _{CB} = 10 V f = 100KHz for NPN types for PNP types			400 600	pF pF

* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

TO-3 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	11.00		13.10	0.433		0.516
B	0.97		1.15	0.038		0.045
C	1.50		1.65	0.059		0.065
D	8.32		8.92	0.327		0.351
E	19.00		20.00	0.748		0.787
G	10.70		11.10	0.421		0.437
N	16.50		17.20	0.649		0.677
P	25.00		26.00	0.984		1.023
R	4.00		4.09	0.157		0.161
U	38.50		39.30	1.515		1.547
V	30.00		30.30	1.187		1.193



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